



AMP3132 SOLID STATE HIGH POWER AMPLIFIER

FEATURES

- Class AB linear solid-state GaAsFET design
- Instantaneous wide bandwidth
- Small form factor and light weight
- Suitable for all single channel modulation standards
- Built-in protection circuits
- High reliability and ruggedness



ELECTRICAL SPECIFICATIONS: 8VDC, 25°C

Parameter	Specification	Notes
Operating Frequency Range	26.5 - 40.0 GHz	
Power Output Psat	8 Watt Typ	
Power Output @ P1dB	5 Watt Typ	
Power Gain	38 dB Min	40dB Nominal
Power Gain Flatness	16 dB p-p Max	Constant input power
Input / Output Return Loss	-10 dB Max	Relative to 50 Ohm
Noise Figure	12 dB Max	
Harmonics	<-30 dBc Typ	At rated Pout
Spurious	-60 dBc Max	Non-harmonics
Operating Voltage	8 VDC Nom	
Current Consumption	16 Amp Typ	At rated Pout
Input Power protection	+3 dBm Max	<10 Sec without damage
Load VSWR Protection	5 : 1 Max	<1 minute at rated Pout

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Case Temperature	-20 to +65 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non-condensing

MECHANICAL SPECIFICATIONS

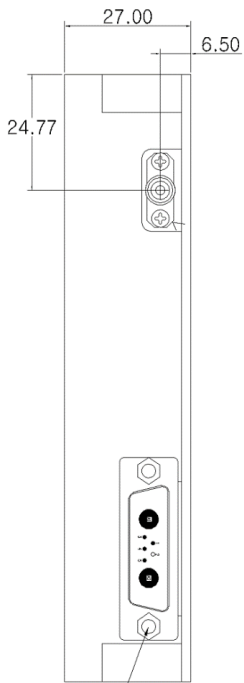
Parameter	Specification	Notes
Dimensions	100 x 130 x 27 mm	Excluding connectors
Weight	1.5 Kg	
RF Connectors In/Out	2.92 mm K Type female	
DC Power / Interface Connector	7-Pin Hybrid D-Sub	
Cooling	External Heatsink	Forced air required

D-SUB CONNECTOR PIN ASSIGNMENT

Pin	Function	Description
1	N/C	Reserved
2	N/C	Reserved
3	CURRENT SENSOR	I _b @20mV/100mA Typ
4	TEMP SENSOR	V _T @10mV/°C + 500mV Typ
5	SHUTDOWN	TTL
A1	VDD	8VDC
A2	GND	Ground

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OUTLINE DRAWING



2X UNC #4-40 Tapping

